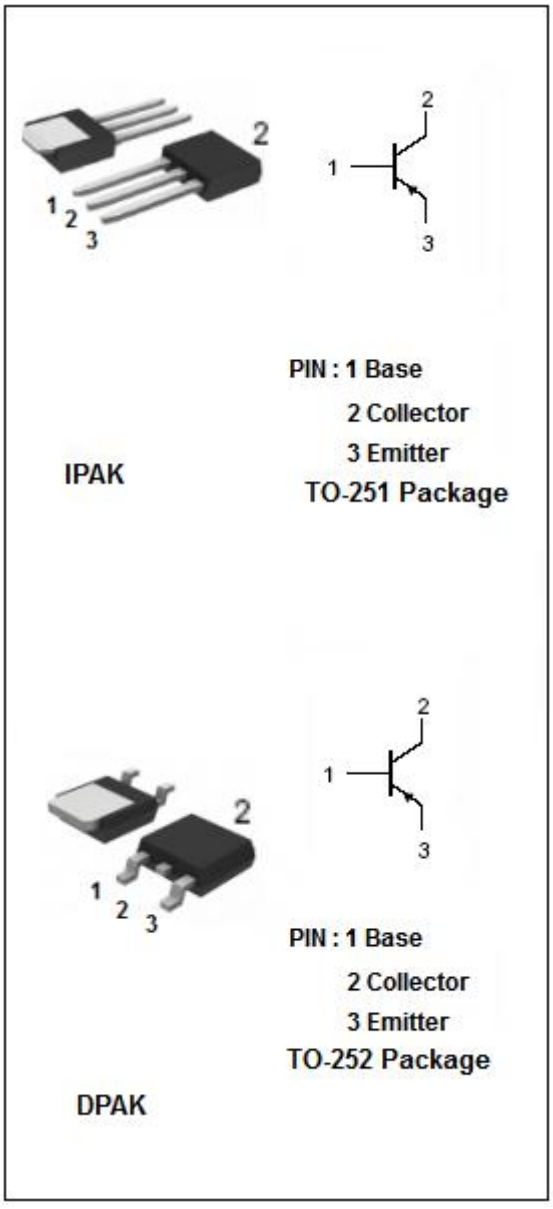
isc Silicon PNP Power Transistor 2SB1184

DESCRIPTION

- Low $V_{CE(sat)}$
- Small and slim package
- Complements the 2SD1760/2SD1864
- 100% tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power dissipation



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @ T_C=25℃	1.0	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -200mA			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -200mA			-1.5	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -50uA; I_B= 0	-60			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; I_B= 0	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -50uA; I_C= 0	-5			V
I_{CBO}	Collector Cutoff Current	V_{CB}= -20V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-1.0	μA
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -3V	82		390	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1.0MHz		70		pF
f_T	Current-Gain—Bandwidth Product	I_C= -500mA; V_{CE}= -5V		50		MHz

◆ **h_{FE} Classifications**

P	Q	R
82-180	120-270	180-390

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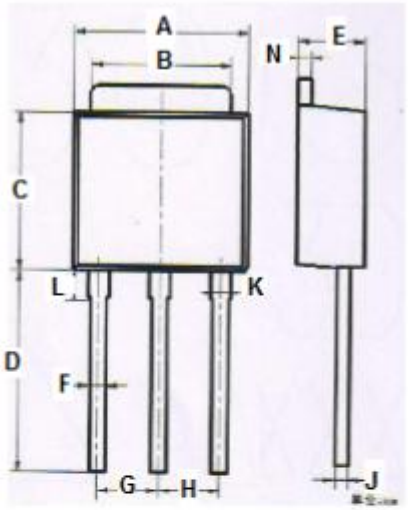
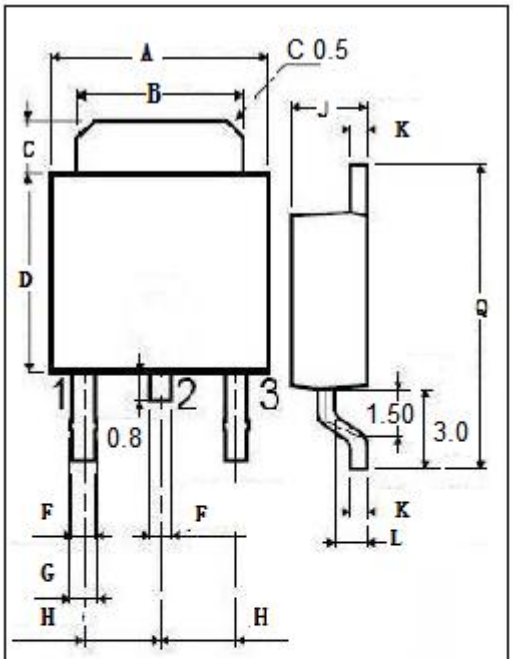
Outline Drawing



DIM	mm MIN	MAX
A	6.40	6.48
B	5.10	5.50
C	5.80	6.20
D	9.20	9.60
E	2.20	2.40
F	0.50	0.70
G	2.09	2.49
H	2.09	2.49
J	0.40	0.60
K	0.70	0.90
L	1.60	2.00
N	0.40	0.60



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1